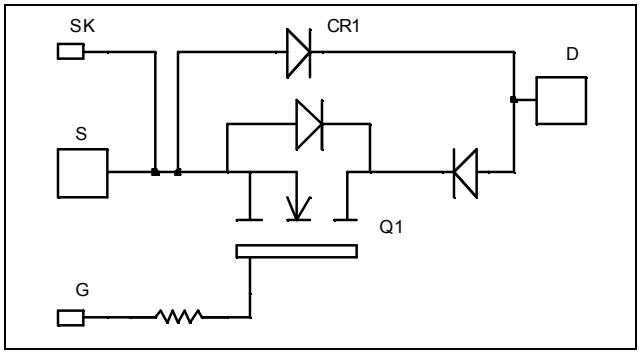
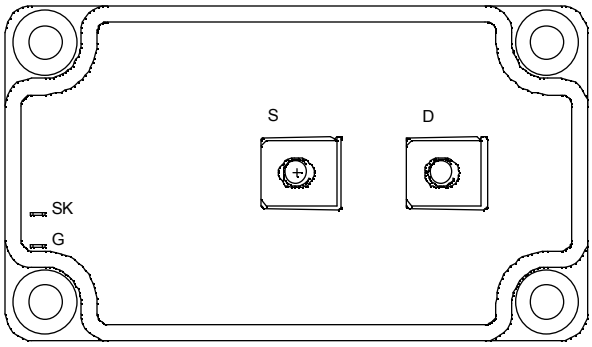
APTM50UM13SAG

Single switch
Series & parallel diodes
MOSFET Power Module

V_{DSS} = 500V
R_{DSon} = 13mΩ typ @ Tj = 25°C
I_D = 335A @ Tc = 25°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		500	V
I_D	Continuous Drain Current	T_c = 25°C	335	A
		T_c = 80°C	250	
I_{DM}	Pulsed Drain current		1340	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		15	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	3290	W
I_{AR}	Avalanche current (repetitive and non repetitive)		71	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 500V	T_j = 25°C			400	µA
		V_{GS} = 0V, V_{DS} = 400V	T_j = 125°C			2000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 167.5A			13	15	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 20mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		42.2		nF
C_{oss}	Output Capacitance			8.24		
C_{rss}	Reverse Transfer Capacitance			0.42		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 250V I_D =335A		800		nC
Q_{gs}	Gate – Source Charge			200		
Q_{gd}	Gate – Drain Charge			420		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 333V I_D = 335A R_G = 0.8Ω		21		ns
T_r	Rise Time			42		
$T_{d(off)}$	Turn-off Delay Time			96		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 333V I_D = 335A, R_G = 0.8Ω		4		mJ
E_{off}	Turn-off Switching Energy			4.16		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 333V I_D = 335A, R_G =0.8Ω		6.32		mJ
E_{off}	Turn-off Switching Energy			4.64		

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=200V	T_j = 25°C			750	µA
			T_j = 125°C			1000	
I_F	DC Forward Current		T_c = 85°C		240		A
V_F	Diode Forward Voltage	I_F = 240A			1.1	1.15	V
		I_F = 480A			1.4		
		I_F = 240A	T_j = 125°C		0.9		
t_{rr}	Reverse Recovery Time	I_F = 240A V_R = 133V di/dt = 800A/µs	T_j = 25°C		31		ns
			T_j = 125°C		60		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		240		nC
			T_j = 125°C		1000		

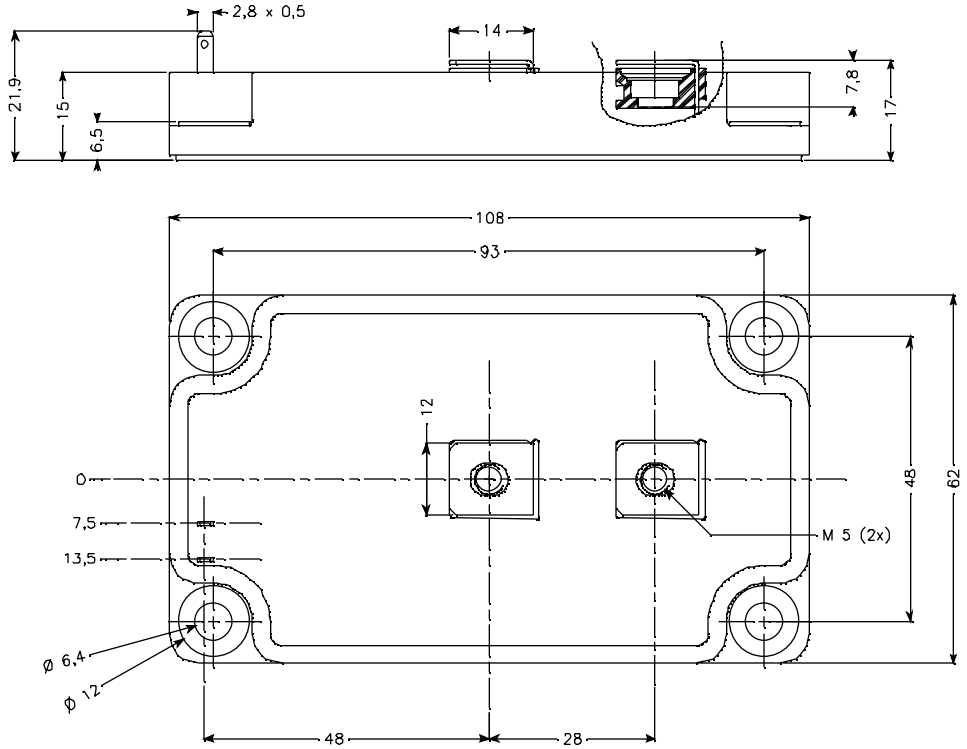
Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			1500	µA
			T_j = 125°C			3000	
I_F	DC Forward Current		T_c = 70°C		360		A
V_F	Diode Forward Voltage	I_F = 360A			1.6	1.8	V
		I_F = 720A			1.9		
		I_F = 360A	T_j = 125°C		1.4		
t_{rr}	Reverse Recovery Time	I_F = 360A V_R = 400V di/dt = 1000A/µs	T_j = 25°C		130		ns
			T_j = 125°C		170		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		1.32		µC
			T_j = 125°C		5.5		

Thermal and package characteristics

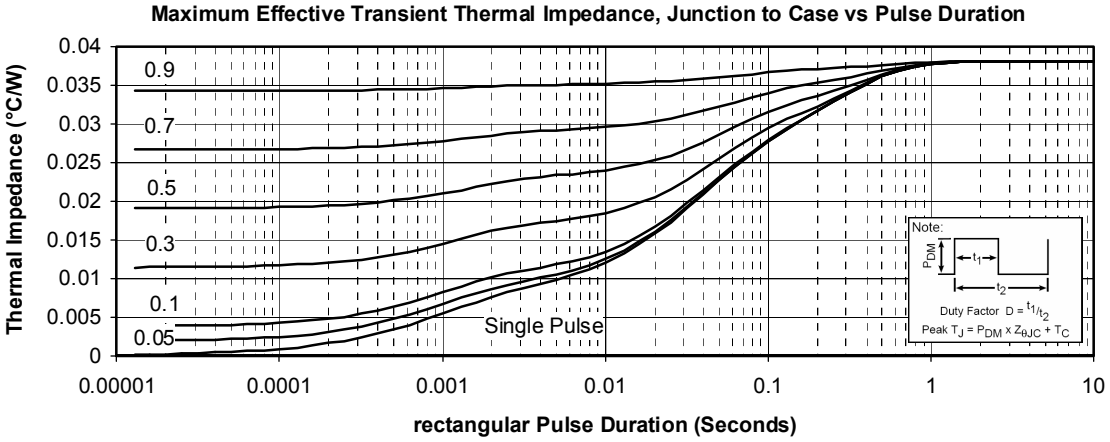
Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	Transistor				0.038	°C/W
		Series diode				0.23	
		Parallel diode				0.16	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

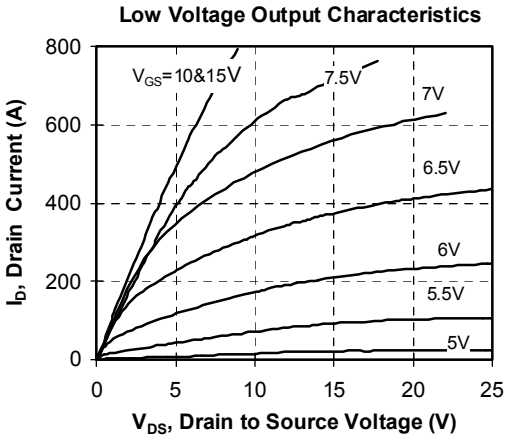
SP6 Package outline (dimensions in mm)

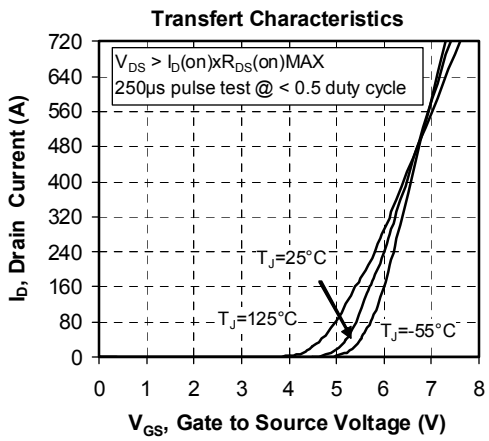


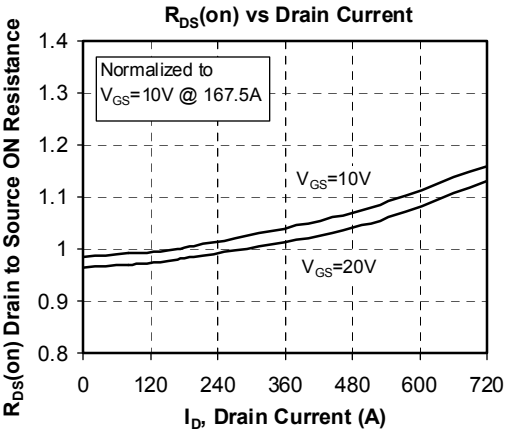
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

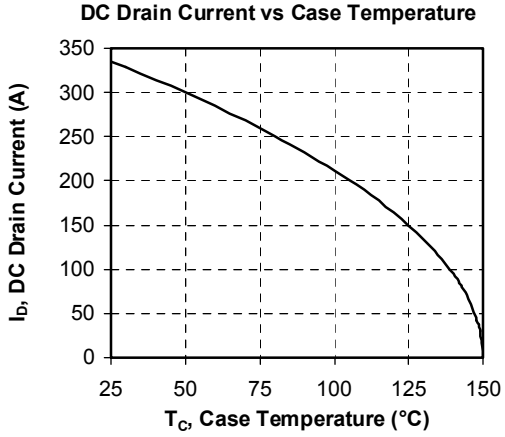
Typical Performance Curve



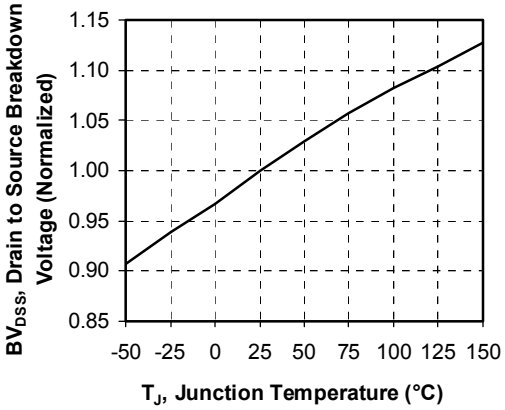




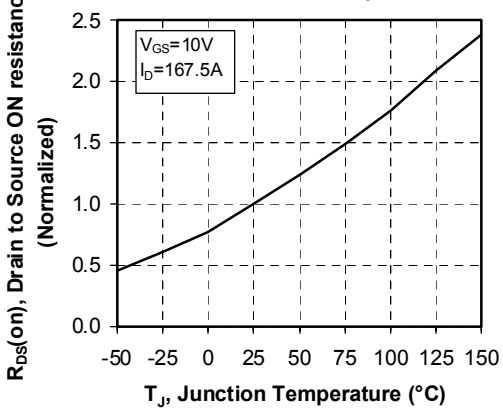




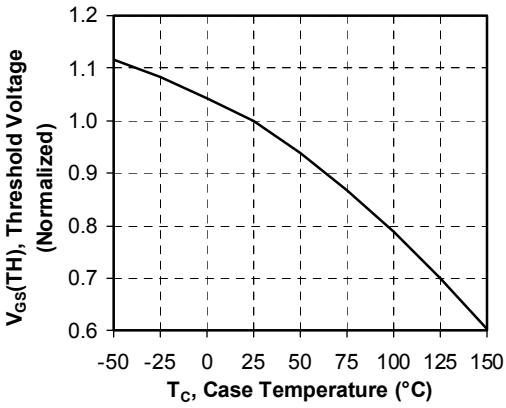
Breakdown Voltage vs Temperature



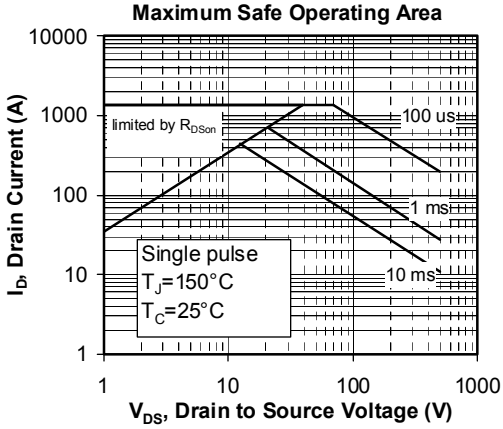
ON resistance vs Temperature



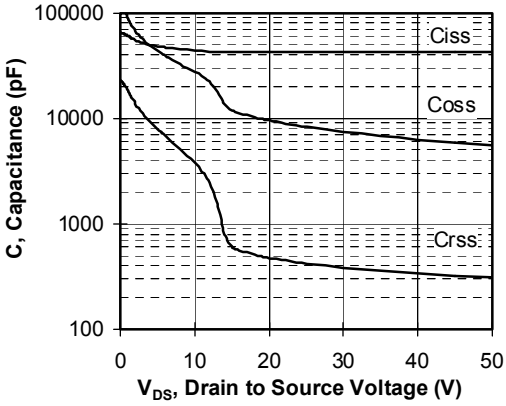
Threshold Voltage vs Temperature



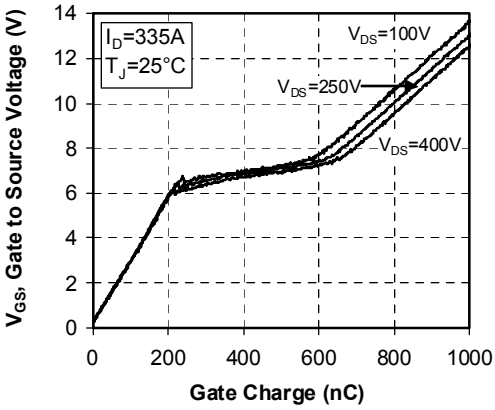
Maximum Safe Operating Area



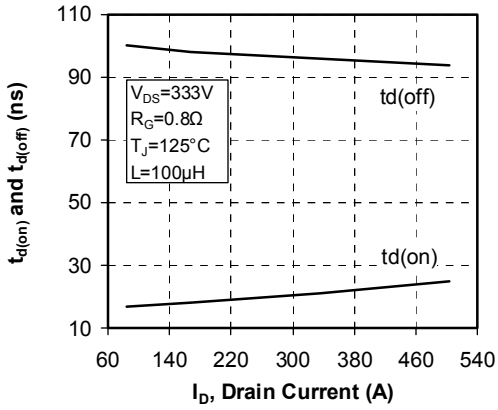
Capacitance vs Drain to Source Voltage



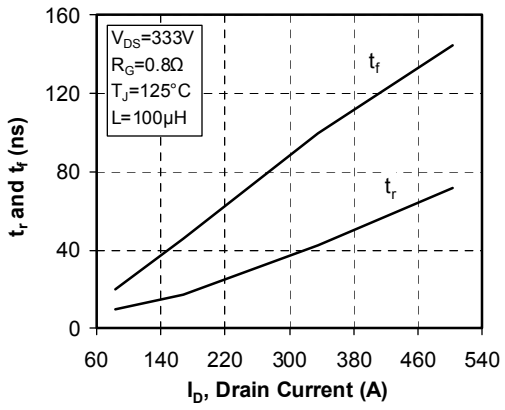
Gate Charge vs Gate to Source Voltage



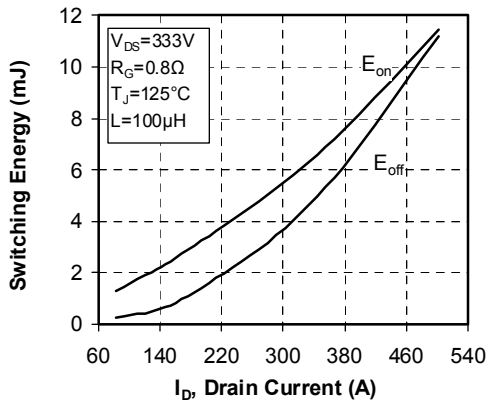
Delay Times vs Current



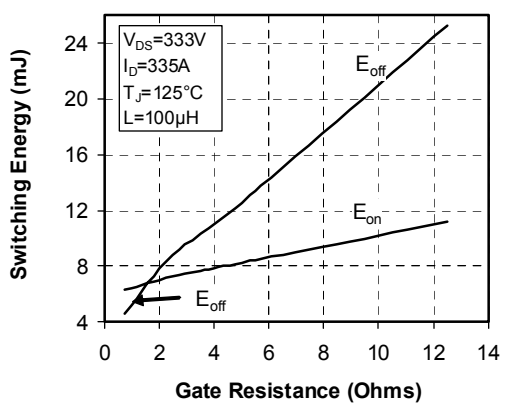
Rise and Fall times vs Current



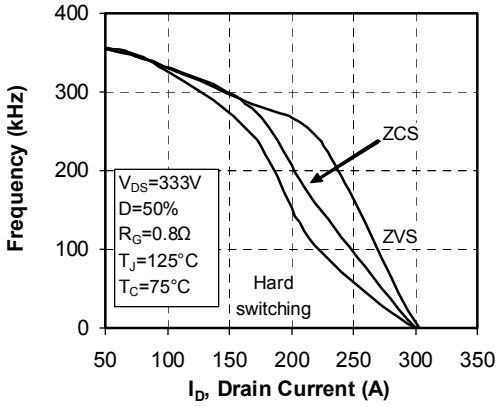
Switching Energy vs Current



Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage